

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1-25 (Cancelled).

Claim 26 (Previously presented): Energy storage device comprising at least one anode, a dielectric and a cathode, in which the elements are coated in part at least by a protective layer formed of a metal or metal alloy having a sufficient thermomechanical resistance to absorb thermomechanical deformations without causing fissures to appear, the metal or the metal alloy having an expansion coefficient less than $6 \cdot 10^{-6} \text{ } ^\circ\text{C}^{-1}$.

Claim 27 (Previously presented): Device according to claim 26, the protective layer being formed of a metal chosen among the group W, Ta, Mo, and Zr.

Claim 28 (Previously presented): Device according to claim 26, the protective layer being formed of a nitrated alloy chosen among the group WN_x , TaN_x , MoN_x , ZrN_x , TiN_x , and AlN_x , where $x < 1$.

Claim 29 (Previously presented): Device according to claim 26, comprising at least one other protective layer formed of a metal or metal alloy having a sufficient thermomechanical resistance to absorb thermomechanical deformations without causing fissures to appear.

Claim 30 (Previously presented): Device according to claim 29, wherein another protective layer is formed of a metal having a Vickers hardness less than 50.

Claim 31 (Previously presented): Device according claim 30, wherein the metal is chosen among the group Pd, Pt, and Au.

Claim 32 (Previously presented): Device according to claim 26, further comprising an electrically insulating layer.

Claim 33 (Previously presented): Device according to claim 32, wherein the insulating layer is located between the elements of the device and the metallic protection layer(s).

Claim 34 (Currently amended): Device according to claim 32, wherein the electrically insulating layer is an oxide.

Claim 35 (Previously presented): Device according to claim 34, wherein the oxide is chosen among the oxides of Mg, Ca, Be, Ce, Si, Al, Ta and La.

Claim 36 (Currently amended): Device according to claim 32, wherein the electrically insulating layer is a sulphide.

Claim 37 (Currently amended): Device according to claim 32, wherein the electrically insulating layer is a nitride.

Claim 38 (Previously presented): Device according to claim 37, wherein the nitride is chosen among Si_3N_4 and BN.

Claim 39 (Previously presented): Device according to claim 32, wherein the insulating layer is a carbide.

Claim 40 (Previously presented): Device according to claim 39, wherein the carbide is chosen among SiC, B_4C , and WC.

Claim 41 (Previously presented): Device according to claim 26, wherein the elements are encapsulated in the protecting and/or insulating layer(s).

Claim 42 (Withdrawn): Method for protecting an energy storage device comprising the coating of a part at least of the device by a protective layer formed of a metal or metal alloy having a sufficient thermomechanical resistance to absorb thermomechanical deformations without causing fissures to appear, the metal or the metal alloy having an expansion coefficient less than $6.10^{-6} \text{ } ^\circ\text{C}^{-1}$.

Claim 43 (Withdrawn): Method according to claim 42, comprising the coating of a part at least of the device by a protective layer formed of a metal having a Vickers hardness less than 50.

Claim 44 (Withdrawn): Method according to claim 42, where the coating(s) are formed by physical vapour deposition or evaporation.

Claim 45 (Withdrawn): Method according to claim 42, comprising, prior to the coating(s) by metallic layer(s), the step of coating by an electrically insulating layer.

Claim 46 (Withdrawn): Method according to claim 45, in which the insulating layer is a ceramic chosen among ZnS, Si₃N₄, BN, SiC, B₄C, WC, MgAl₂O₄ and the oxides of Mg, Ca, Be, Ce, La, Si, Al or Ta.

Claim 47 (Withdrawn): Method according to claim 45, wherein the coating by an insulating layer is carried out by physical vapour deposition, radiofrequency sputtering or ion beam sputtering.

Claim 48 (Withdrawn): Method according to claim 45, comprising, prior to the coating by the insulating layer, a step of pre-encapsulation.

Claim 49 (Withdrawn): Method according to claim 48, comprising the elimination of the pre-encapsulation layer before the coating by the insulating layer.

Claim 50 (Withdrawn): Method for protecting a microbattery comprising the encapsulation of the microbattery by the method according to claim 42.